

7MBP50VDA120-50

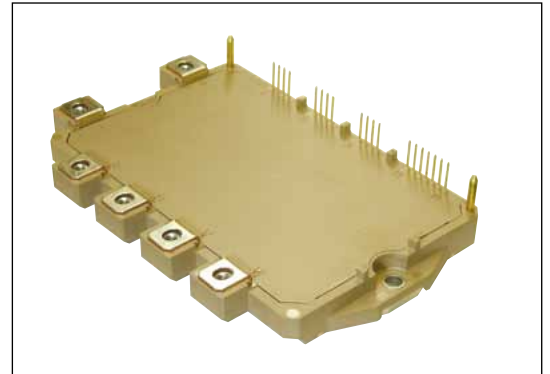
IGBT Modules

IGBT MODULE (V series)

1200V / 50A / IPM

■ Features

- Temperature protection provided by directly detecting the junction temperature of the IGBTs
- Low power loss and soft switching
- High performance and high reliability IGBT with overheating protection
- Higher reliability because of a big decrease in number of parts in built-in control circuit



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings ($T_c=25^\circ\text{C}$, $V_{cc}=15\text{V}$ unless otherwise specified)

Items	Symbol	Min.	Max.	Units		
Collector-Emitter Voltage (*1)	V_{CES}	0	1200	V		
Short Circuit Voltage	V_{SC}	400	800	V		
Inverter	Collector Current	DC	I_C	-	50	A
		1ms	I_{cp}	-	100	A
		Duty=100% (*2)	$-I_C$	-	50	A
Collector Power Dissipation	1 device (*3)	P_C	-	250	W	
Brake	Collector Current	DC	I_C	-	25	A
		1ms	I_{cp}	-	50	A
	Forward Current of Diode		I_F	-	25	A
	Collector Power Dissipation	1 device (*3)	P_C	-	187	W
Supply Voltage of Pre-Driver (*4)	V_{CC}	-0.5	20	V		
Input Signal Voltage (*5)	V_{in}	-0.5	$V_{CC}+0.5$	V		
Alarm Signal Voltage (*6)	V_{ALM}	-0.5	V_{CC}	V		
Alarm Signal Current (*7)	I_{ALM}	-	20	mA		
Junction Temperature	T_J	-	150	$^\circ\text{C}$		
Operating Case Temperature	T_{opr}	-20	110	$^\circ\text{C}$		
Storage Temperature	T_{stg}	-40	125	$^\circ\text{C}$		
Solder Temperature (*8)	T_{sol}	-	260	$^\circ\text{C}$		
Isolating Voltage (*9)	V_{iso}	-	AC2500	Vrms		
Screw Torque	Terminal (M4)	-	-	-		
	Mounting (M4)	-	-	1.7	Nm	

Note *1: V_{CES} shall be applied to the input voltage between terminal P-(U, V, W) and (U, V, W, B)-N.

Note *2: Duty=125 $^\circ\text{C}/R_{th(j-c)}$ / ($I_F \times V_F$ Max.) $\times 100$

Note *3: $P_C=125^\circ\text{C}/R_{th(j-c)}$ (Inverter & Brake)

Note *4: V_{CC} shall be applied to the input voltage between terminal No.4 and 1, 8 and 5, 12 and 9, 14 and 13.

Note *5: V_{in} shall be applied to the input voltage between terminal No.3 and 1, 7 and 5, 11 and 9, 15~18 and 13.

Note *6: V_{ALM} shall be applied to the voltage between terminal No.2 and 1, 6 and 5, 10 and 9, 19 and 13.

Note *7: I_{ALM} shall be applied to the input current to terminal No.2, 6, 10 and 19.

Note *8: Immersion time 10 \pm 1sec. 1time.

Note *9: Terminal to base, 50/60Hz sine wave 1min. All terminals should be connected together during the test.

● Electrical Characteristics (T_J=25°C, V_{cc}=15V unless otherwise specified)

Items	Symbol	Conditions	Min.	Typ.	Max.	Units		
Inverter	Collector Current at off signal input	I _{CES}	V _{CE} =1200V		-	-	1.0	mA
	Collector-Emitter saturation voltage	V _{CE(sat)}	I _c =50A	Terminal	-	-	2.25	V
				Chip	-	1.70	-	V
	Forward voltage of FWD	V _F	I _F =50A	Terminal	-	-	2.80	V
Chip				-	2.10	-	V	
Brake	Collector Current at off signal input	I _{CES}	V _{CE} =1200V		-	-	1.0	mA
	Collector-Emitter saturation voltage	V _{CE(sat)}	I _c =25A	Terminal	-	-	2.10	V
				Chip	-	1.70	-	V
	Forward voltage of FWD	V _F	I _F =25A	Terminal	-	-	2.55	V
Chip				-	2.10	-	V	
Switching time	t _{on}	V _{DC} =600V, T _J =125°C, I _c =50A		1.1	-	-	μs	
	t _{off}			-	-	2.1	μs	
	t _{rr}	V _{DC} =600V, I _F =50A		-	-	0.3	μs	
Supply current of P-side pre-driver (per one unit)	I _{ccp}	Switching Frequency= 0-15kHz		-	-	14	mA	
Supply current of N-side pre-driver	I _{ccn}	T _c =-20~110°C		-	-	58	mA	
Input signal threshold voltage	V _{in(th)(on)}	V _{in} -GND	ON	1.2	1.4	1.6	V	
	V _{in(th)(off)}		OFF	1.5	1.7	1.9	V	
Over Current Protection Level	I _{OC}	T _J =125°C		75	-	-	A	
				38	-	-	A	
Over Current Protection Delay time	t _{dOC}	T _J =125°C		-	5	-	μs	
Short Circuit Protection Delay time	t _{sc}	T _J =125°C		-	2	3	μs	
IGBT Chips Over Heating Protection Temperature Level	T _{JOH}	Surface of IGBT Chips		150	-	-	°C	
Over Heating Protection Hysteresis	T _{JH}			-	20	-	°C	
Under Voltage Protection Level	V _{UV}			11.0	-	12.5	V	
Under Voltage Protection Hysteresis	V _H			0.2	0.5	-	V	
Alarm Signal Hold Time	t _{ALM(OC)}	ALM-GND T _c =-20~110°C	V _{cc} ≥ 10V	1.0	2.0	2.4	ms	
	t _{ALM(UV)}			2.5	4.0	4.9	ms	
	t _{ALM(TJOH)}			5.0	8.0	11.0	ms	
Resistance for current limit	R _{ALM}			960	1265	1570	Ω	

● Thermal Characteristics (T_c = 25°C)

Items		Symbol	Min.	Typ.	Max.	Units	
Junction to Case Thermal Resistance (*10)	Inverter	IGBT	R _{th(j-c)Q}	-	-	0.50	°C/W
		FWD	R _{th(j-c)D}	-	-	0.74	°C/W
	Brake	IGBT	R _{th(j-c)Q}	-	-	0.67	°C/W
		FWD	R _{th(j-c)D}	-	-	1.2	°C/W
Case to Fin Thermal Resistance with Compound		R _{th(c-f)}	-	0.05	-	°C/W	

Note *10: For 1device, the measurement point of the case is just under the chip.

● Noise Immunity (V_{dc}=600V, V_{cc}=15V)

Items	Conditions	Min.	Typ.	Max.	Units
Common mode rectangular noise	Pulse width 1μs, polarity ±, 10 min. Judge : no over-current, no miss operating	±2.0	-	-	kV

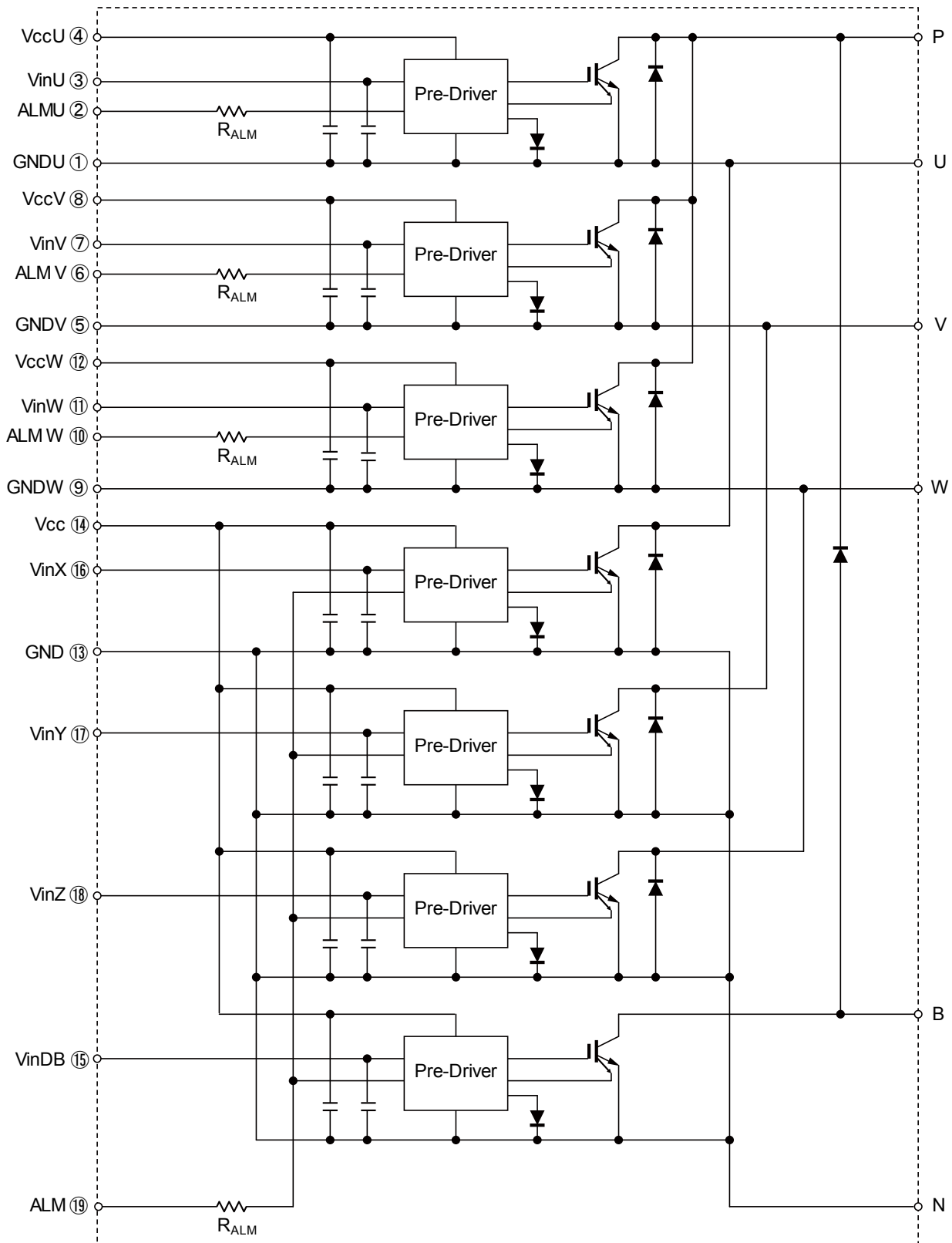
● Recommended Operating Conditions

Items	Symbol	Min.	Typ.	Max.	Units
DC Bus Voltage	V _{DC}	-	-	800	V
Power Supply Voltage of Pre-Driver	V _{CC}	13.5	15.0	16.5	V
Switching frequency of IPM	f _{sw}	-	-	20	kHz
Arm shoot through blocking time for IPM's input signal	t _{dead}	1.0	-	-	μs
Screw Torque (M4)	-	1.3	-	1.7	Nm

● Weight

Items	Symbol	Min.	Typ.	Max.	Units
Weight	W _t	-	290	-	g

■ Block Diagram

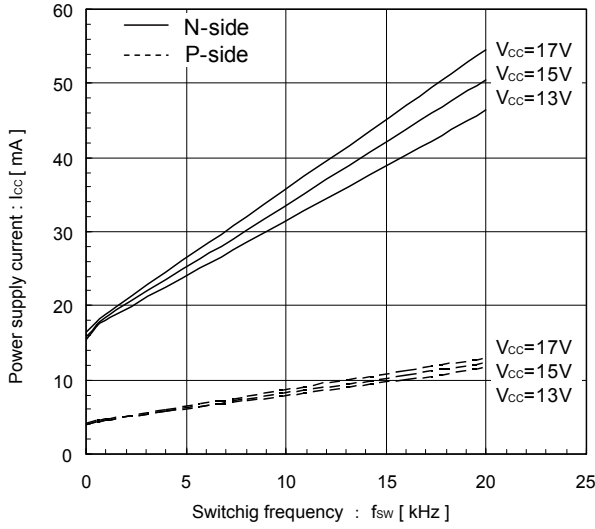


Pre-drivers include following functions

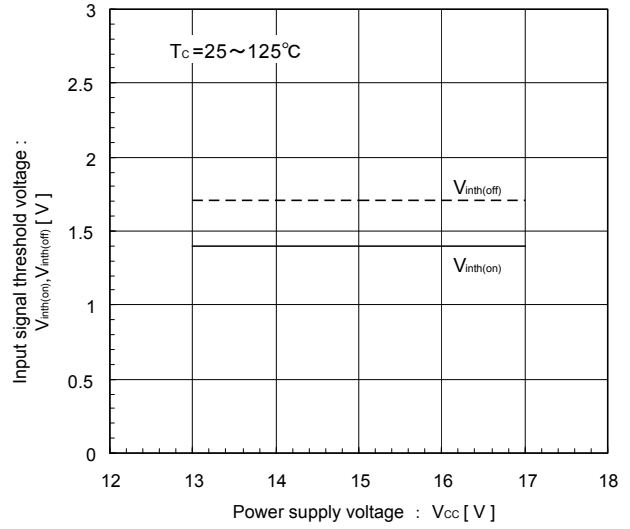
1. Amplifier for driver
2. Short circuit protection
3. Under voltage lockout circuit
4. Over current protection
5. IGBT chip over heating protection

■ Characteristics (Representative)

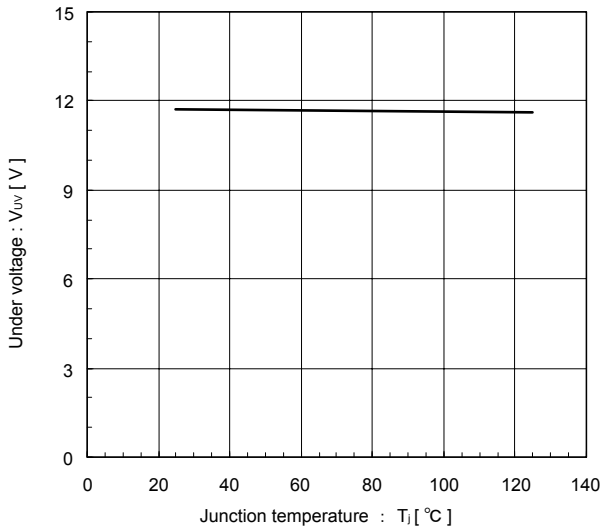
Power supply current vs. Switching frequency
 $T_j = 25^\circ\text{C}(\text{typ.})$



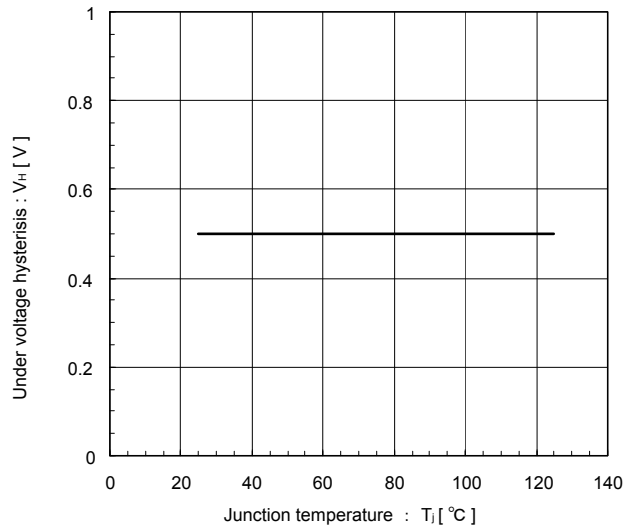
Input signal threshold voltage vs. Power supply voltage (typ.)



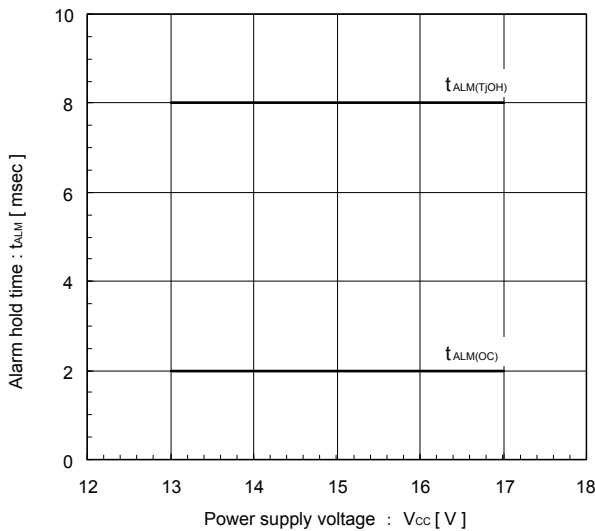
Under voltage vs. Junction temperature (typ.)



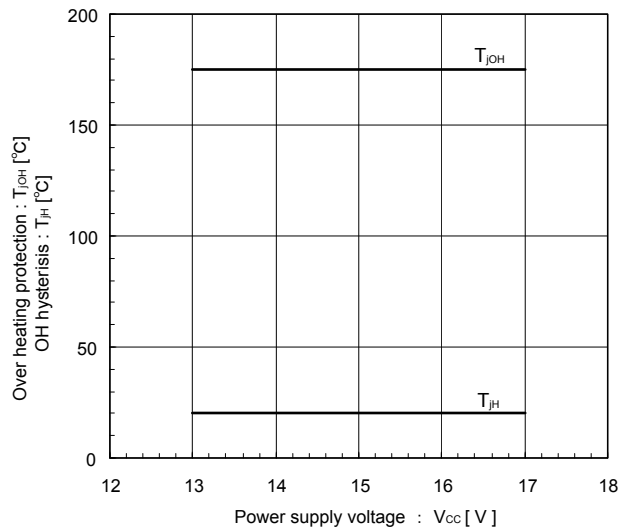
Under voltage hysteresis vs. Junction temperature (typ.)



Alarm hold time vs. Power supply voltage (typ.)

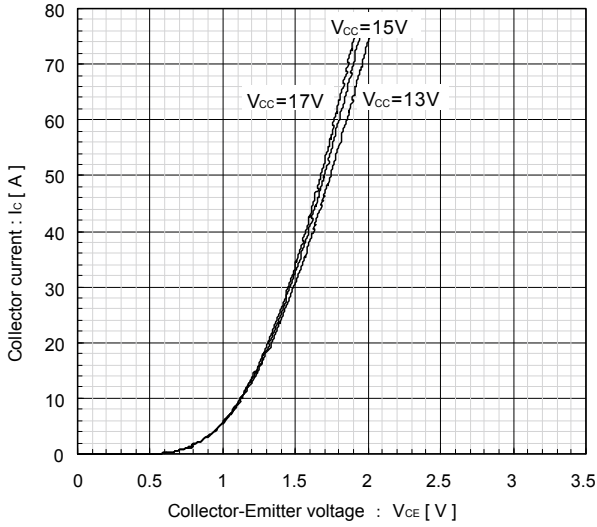


Over heating characteristics
 T_{jOH}, T_{jH} vs. V_{cc} (typ.)

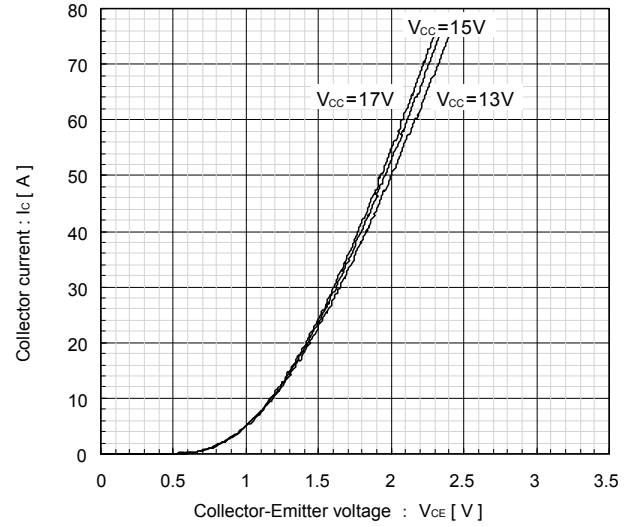


Inverter

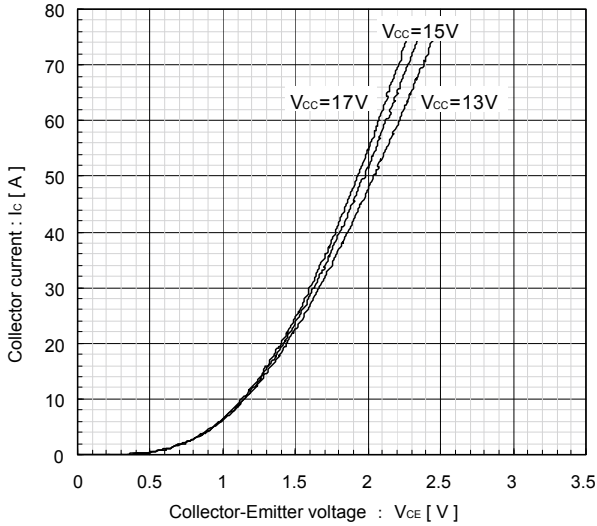
Collector current vs. Collector-Emitter voltage
 $T_j=25^\circ\text{C}$ [Chip] (typ.)



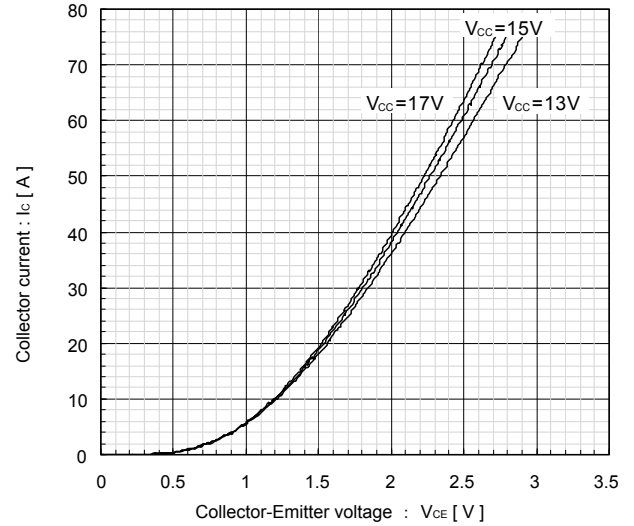
Collector current vs. Collector-Emitter voltage
 $T_j=25^\circ\text{C}$ [Terminal] (typ.)



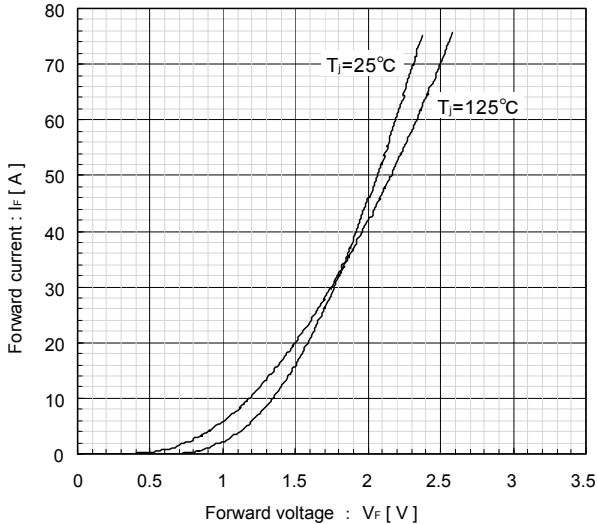
Collector current vs. Collector-Emitter voltage
 $T_j=125^\circ\text{C}$ [Chip] (typ.)



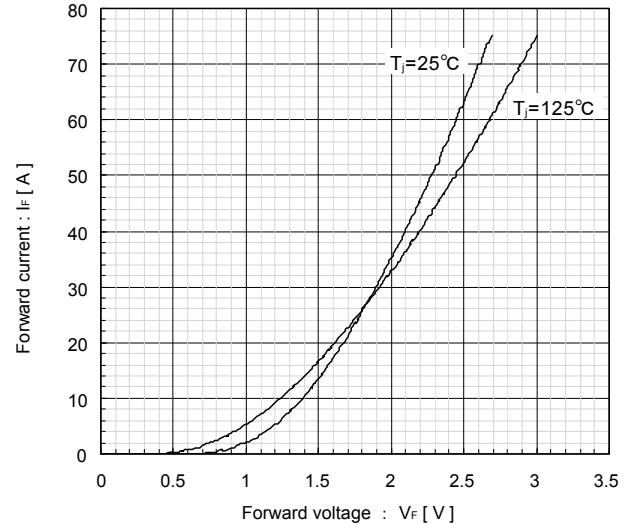
Collector current vs. Collector-Emitter voltage
 $T_j=125^\circ\text{C}$ [Terminal] (typ.)



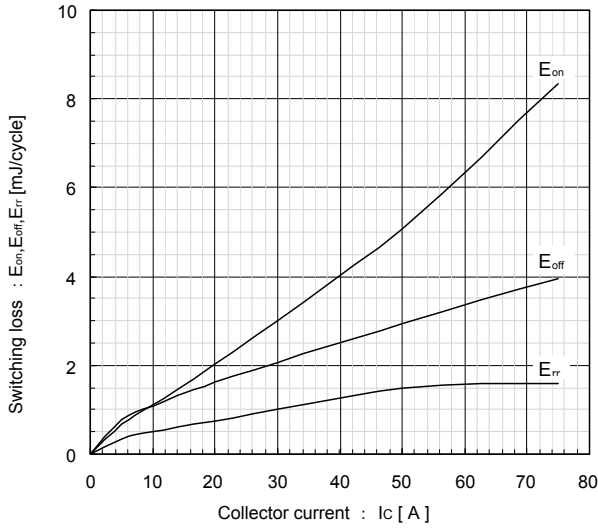
Forward current vs. Forward voltage
 [Chip] (typ.)



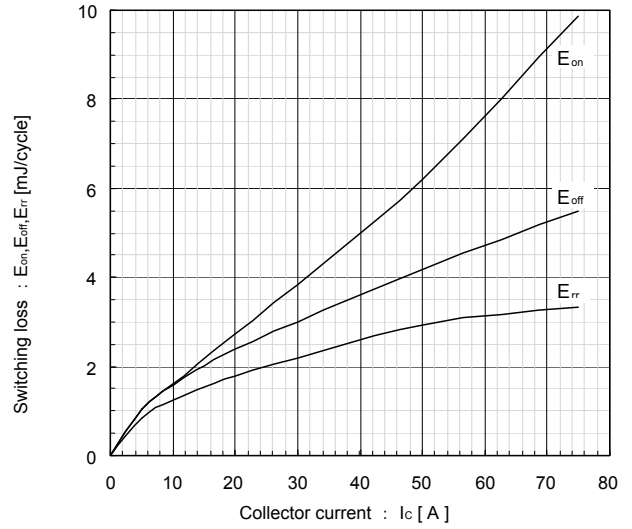
Forward current vs. Forward voltage
 [Terminal] (typ.)



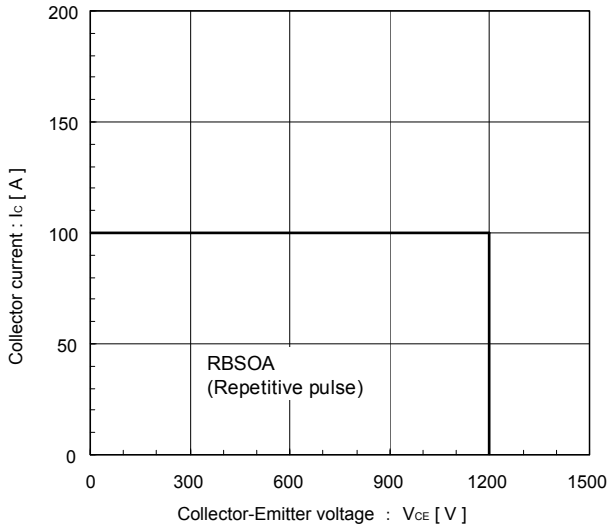
Switching Loss vs. Collector Current (typ.)
 $V_{DC}=600V, V_{CC}=15V, T_J=25^{\circ}C$



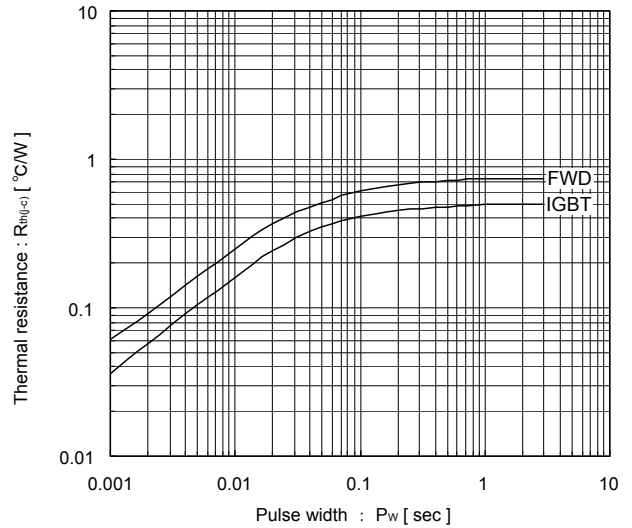
Switching Loss vs. Collector Current (typ.)
 $V_{DC}=600V, V_{CC}=15V, T_J=125^{\circ}C$



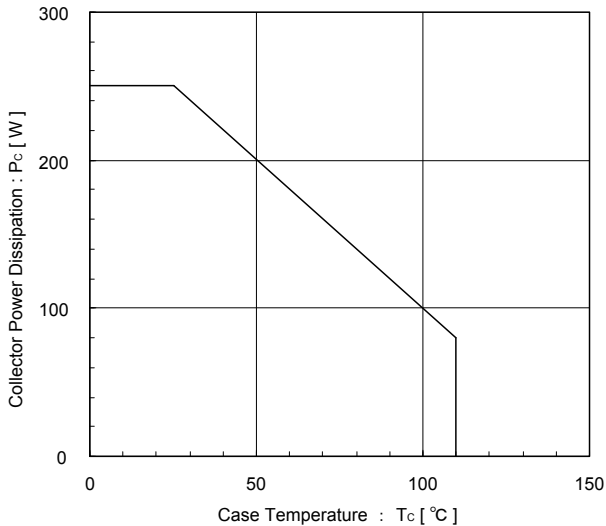
Reversed biased safe operating area
 $V_{CC}=15V, T_J \leq 125^{\circ}C$ [Main Terminal] (min.)



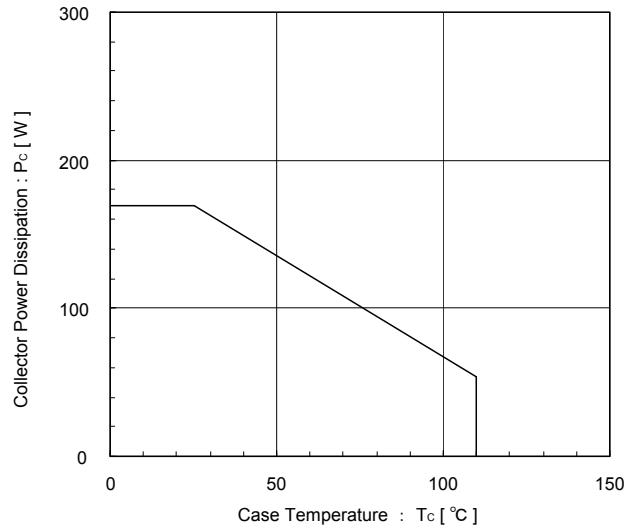
Transient thermal resistance (max.)



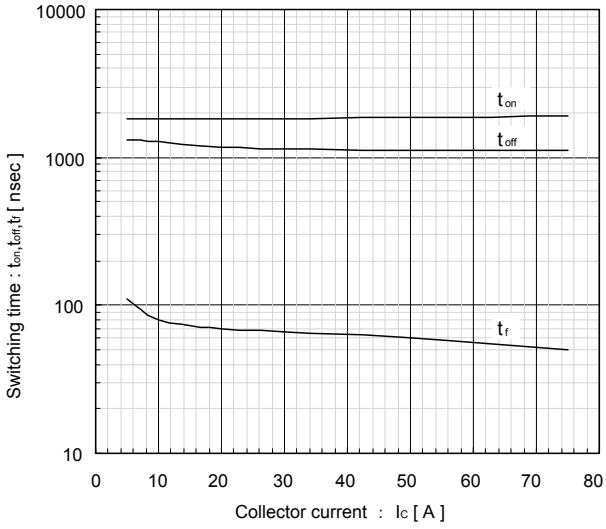
Power derating for IGBT (max.)
 [per device]



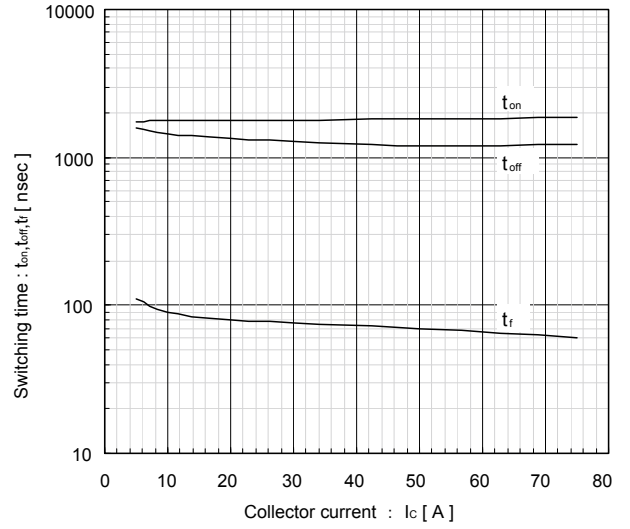
Power derating for FWD (max.)
 [per device]



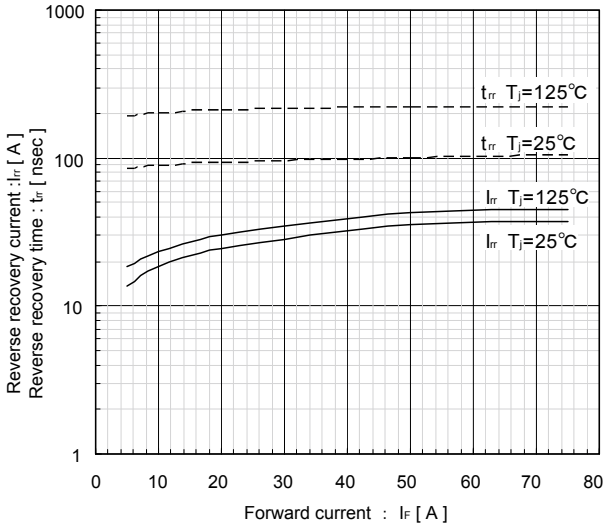
Switching time vs. Collector current (typ.)
 $V_{DC}=600V, V_{CC}=15V, T_J=25^\circ C$



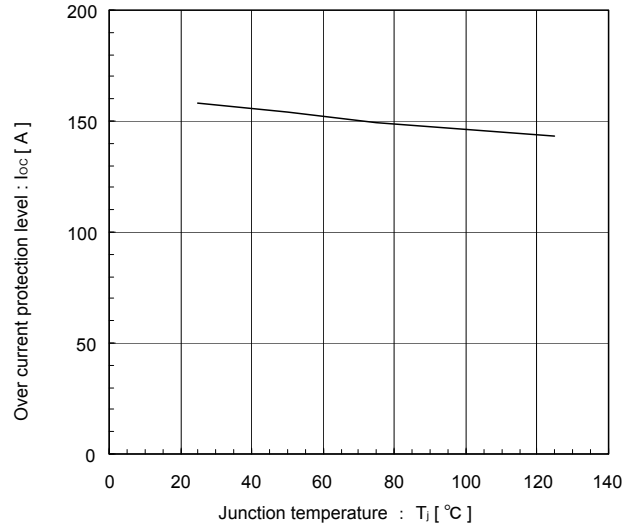
Switching time vs. Collector current (typ.)
 $V_{DC}=600V, V_{CC}=15V, T_J=125^\circ C$



Reverse recovery characteristics (typ.)
 t_{rr}, I_{rr} vs. I_F

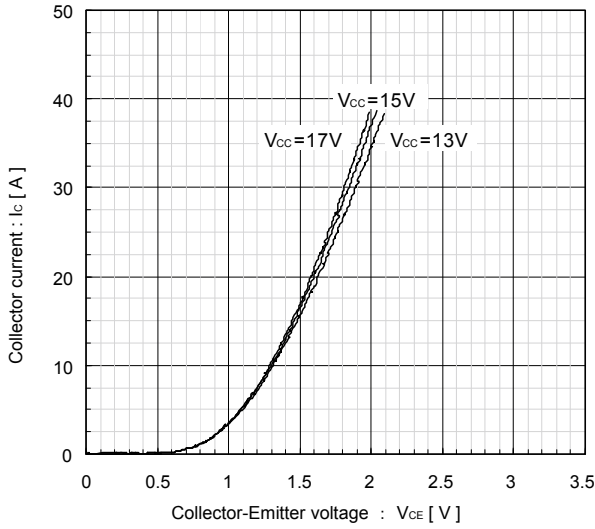


Over current protection vs. Junction temperature (typ.)
 $V_{CC}=15V$

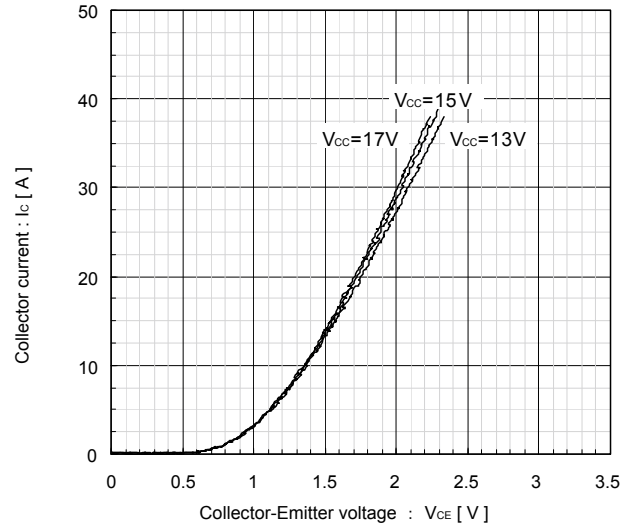


Brake

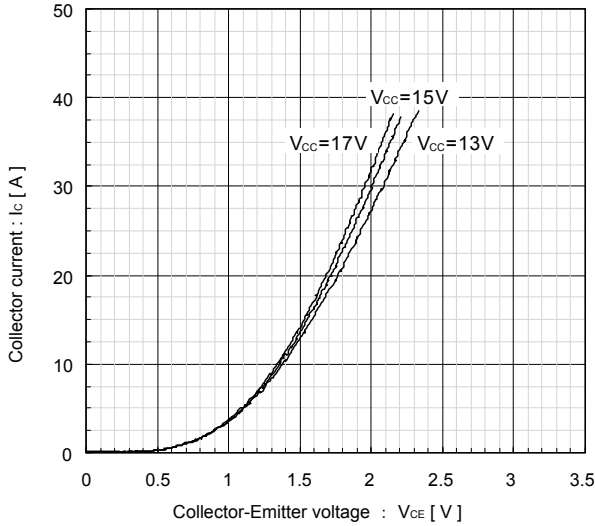
Collector current vs. Collector-Emitter voltage
 $T_j=25^\circ\text{C}$ [Chip] (typ.)



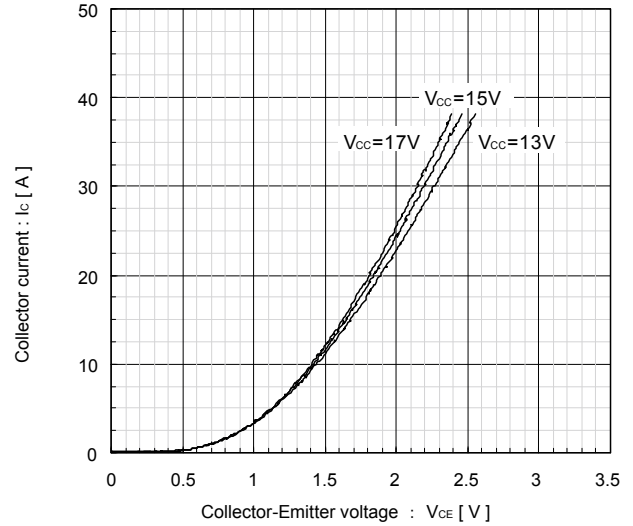
Collector current vs. Collector-Emitter voltage
 $T_j=25^\circ\text{C}$ [Terminal] (typ.)



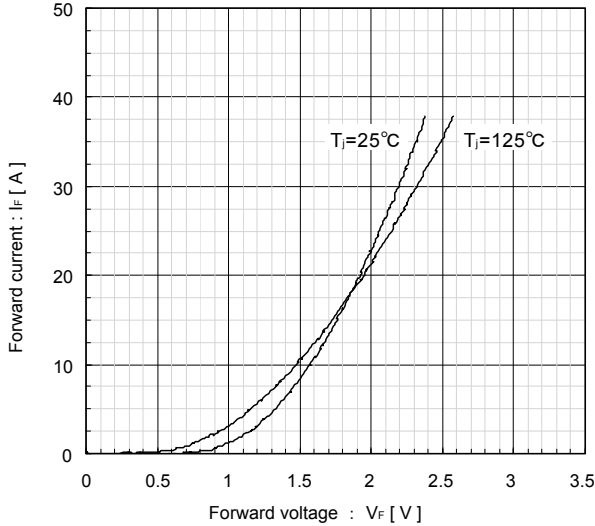
Collector current vs. Collector-Emitter voltage
 $T_j=125^\circ\text{C}$ [Chip] (typ.)



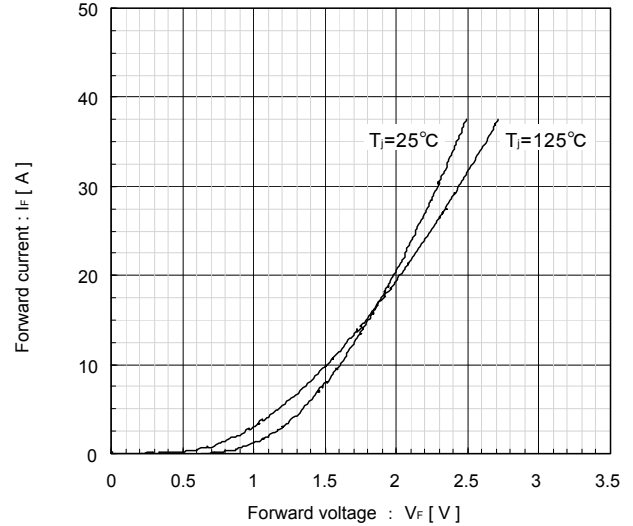
Collector current vs. Collector-Emitter voltage
 $T_j=125^\circ\text{C}$ [Terminal] (typ.)



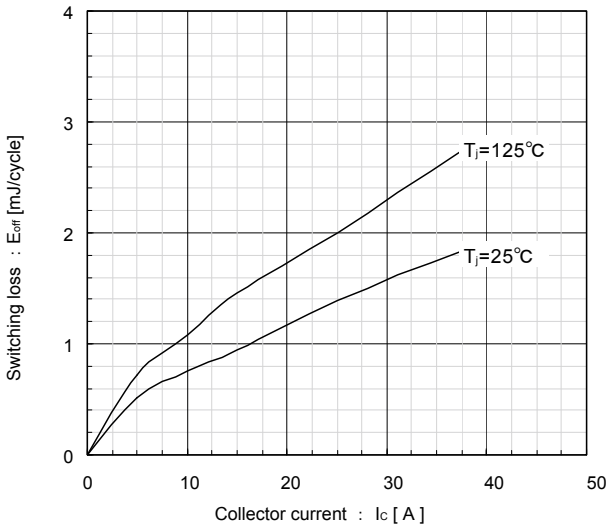
Forward current vs. Forward voltage
 [Chip] (typ.)



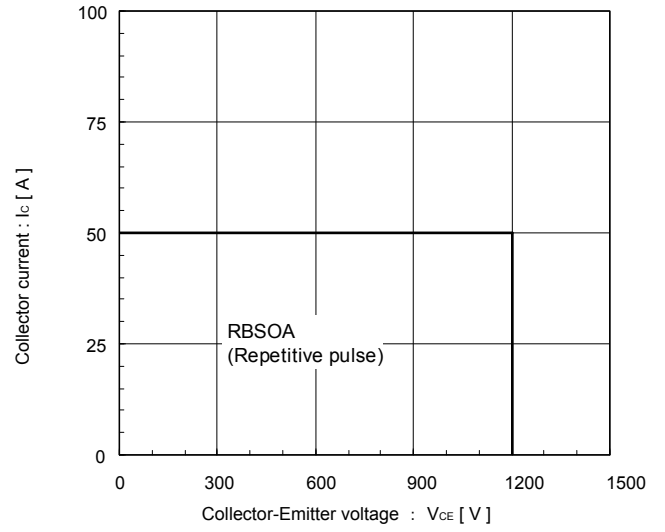
Forward current vs. Forward voltage
 [Terminal] (typ.)



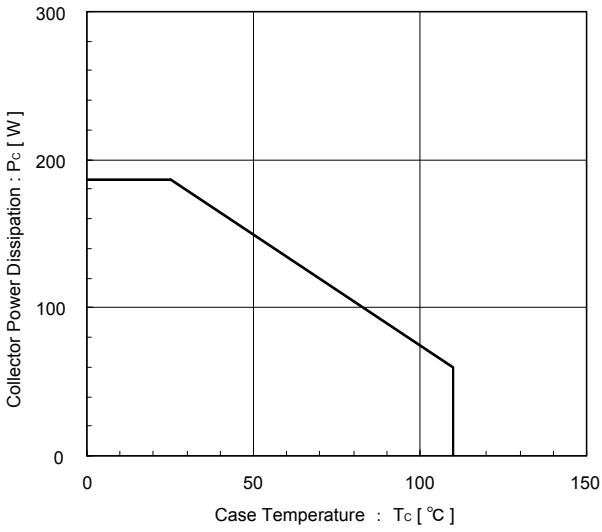
Switching Loss vs. Collector Current (typ.)
 $V_{DC}=600V, V_{CC}=15V$



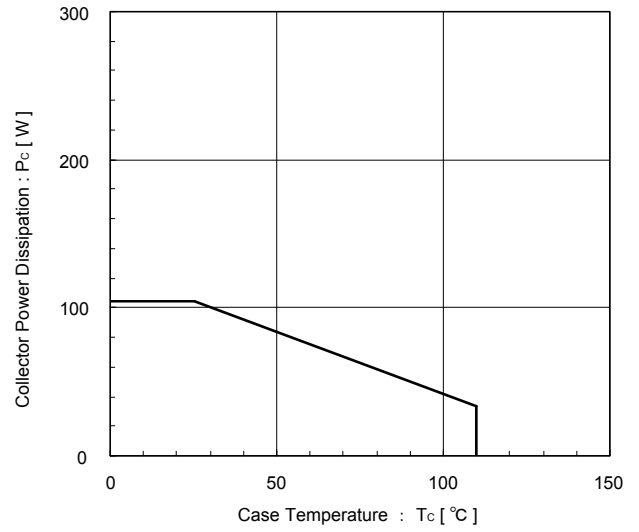
Reversed biased safe operating area
 $V_{CC}=15V, T_j \le 125^\circ C$ [Main Terminal] (min.)



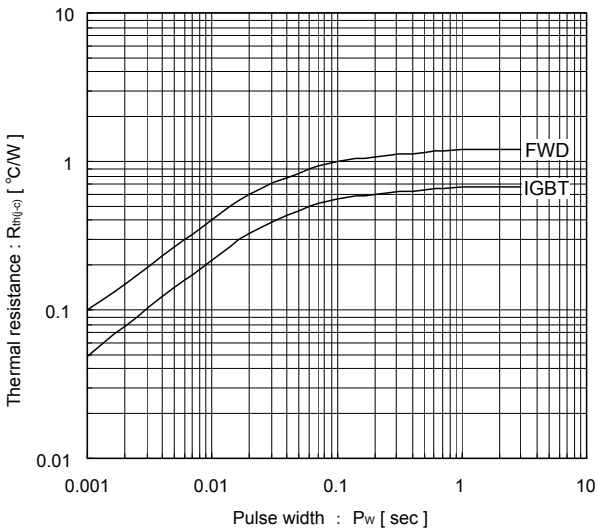
Power derating for IGBT (max.)
 [per device]



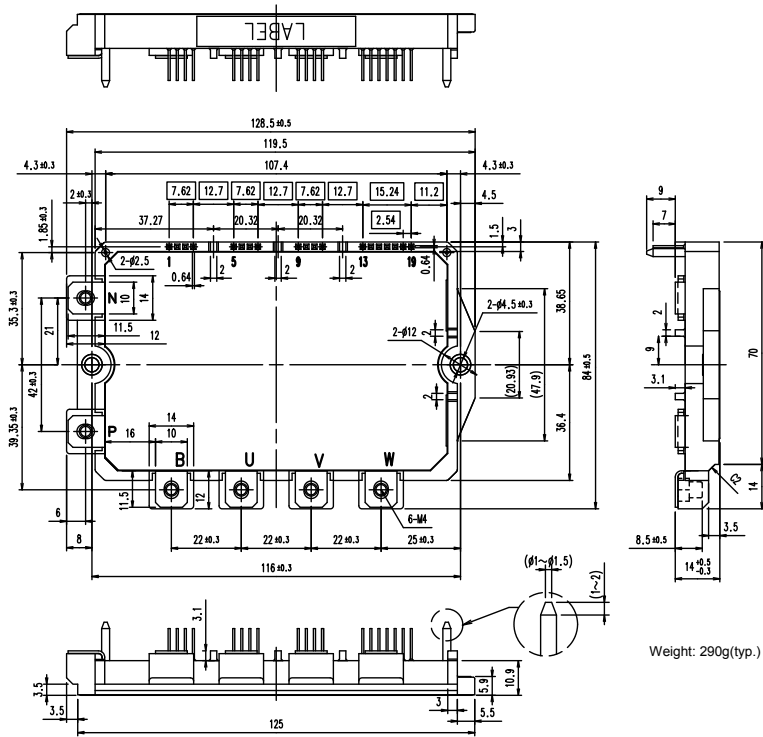
Power derating for FWD (max.)
 [per device]



Transient thermal resistance (max.)



■ Outline Drawings, mm



WARNING

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IGBT Modules

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4 技术资料	www.fujielectric.com.cn/products/semiconductor/model/igbt/technical/
5 安装说明书	www.fujielectric.com.cn/products/semiconductor/model/igbt/mounting/
6 IGBT 损耗模拟软件	www.fujielectric.com.cn/products/semiconductor/model/igbt/simulation/
7 AT-NPC 3-Level 损耗模拟软件	www.fujielectric.com.cn/products/semiconductor/model/igbt/simulation_3level/
8 富士电机技报	www.fujielectric.com.cn/products/semiconductor/journal/
9 产品咨询	www.fujielectric.com.cn/products/semiconductor/contact/
10 产品更改和停产信息	www.fujielectric.com.cn/products/semiconductor/discontinued/